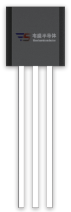
2N6517 TRANSISTOR (NPN)



TO-92

1.EMITTER
2.COLLECTOR
3.BASE

FEATURES

- Complement to 2N6520

ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2N6517	TO-92	Bulk	1000pcs/Bag
2N6517-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	350	V
V_{CEO}	Collector-Emitter Voltage	350	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	0.5	A
P_D	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	200	℃ /W
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃

T_a=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=0.1mA,I_E=0	350			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0	350			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=0.01mA,I_C=0	6			V
Collector cut-off current	I_{CBO}	V_{CB}=250V,I_E=0			0.05	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V,I_C=0			0.05	μA
DC current gain	h_{FE}*	V_{CE}=10V, I_C=1mA	20			
		V_{CE}=10V, I_C=10mA	30			
		V_{CE}=10V, I_C=30mA	30		200	
		V_{CE}=10V, I_C=50mA	20		200	
		V_{CE}=10V, I_C=100mA	15			
Collector-emitter saturation voltage	$V_{CE(sat)}$*	I_C=10mA,I_B=1mA			0.3	V
		I_C=50mA,I_B=5mA			1	V
Base-emitter saturation voltage	$V_{BE\ (sat)}$*	I_C=10mA,I_B=1mA			0.75	V
		I_C=20mA,I_B=2mA			0.85	V
		I_C=30mA,I_B=3mA			0.9	V
Base-emitter voltage	V_{BE}*	V_{CE}=10V, I_C=100mA			2	V
Transition frequency	f_T*	V_{CE}=20V,I_C=10mA,f=20MHz	40		200	MHz
Collector output capacitance	C_{ob}	V_{CB}=20V,I_E=0, f=1MHz			6	pF

*Pulse test: pulse width ≤300μs, duty cycle≤ 2.0%.